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Sheet <u>l</u> of 3 Applicants: Choi et al. Title: METHOD OF ETCHING OXIDE WITH HIGH SELECTIVITY

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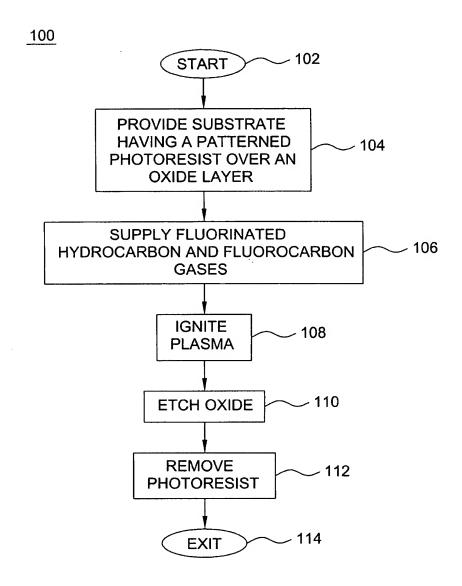


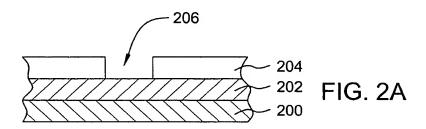
FIG. 1

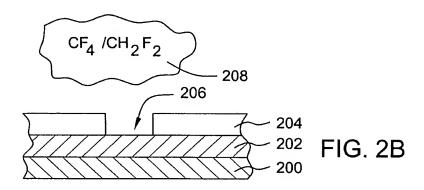
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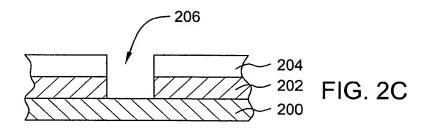
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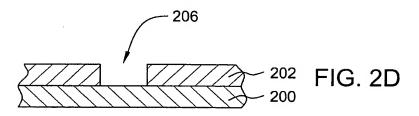
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